

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S22	793	(257/635 or 257/637).ccls. and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 15:35
S23	682	(257/640 or 257/643).ccls. and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 15:41
S24	691	(257/758).ccls. and @ad<"20030711" and (barrier with (dielectric or insulat\$4 or ILD or IMD))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 15:45
S25	250	(257/759.ccls. or 257/760.ccls.) and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 15:48
S26	112	(257/773).ccls. and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 15:52
S27	30	semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" and (plug or conductor or via or contact) with (polysilicon and copper and tungsten)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 20:37
S28	1044	semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 16:09